

AMENDMENTS TO THE SPECIFICATION

Please amend ¶[0016] as follows:

FIG. 5 is a timing diagram of charge storage integration according to a first embodiment of the invention ~~a top down diagram of an exemplary pixel circuit according to a first embodiment of the invention;~~

Please amend ¶[0017] as follows:

FIG. 6 is a timing diagram of charge readout according to a first embodiment of the invention ~~a top down diagram of an exemplary pixel circuit according to a second embodiment of the invention;~~

Please amend ¶[0018] as follows:

FIG. 7 is a timing diagram of charge readout according to a second embodiment of the invention ~~a top down diagram of an exemplary pixel circuit according to a third embodiment of the invention;~~

Please amend ¶[0019] as follows:

FIG. 8 is a timing diagram of charge readout according to a third embodiment of the invention ~~a timing diagram of charge storage integration according to a first embodiment of the invention;~~

Please amend ¶[0020] as follows:

FIG. 9 is a top down diagram of an exemplary pixel circuit according to a first embodiment of the invention ~~a timing diagram of charge readout according to a first embodiment of the invention;~~

Please amend ¶[0021] as follows:

FIG. 10 is a top down diagram of an exemplary pixel circuit according to a second embodiment of the invention ~~a timing diagram of charge readout according to a second embodiment of the invention;~~

Please amend ¶[0022] as follows:

FIG. 11 is a top down diagram of an exemplary pixel circuit according to a third embodiment of the invention ~~a timing diagram of charge readout according to a third embodiment of the invention;~~ and

Please amend ¶[0031] as follows:

Subsequent to the second reset of storage node 306[[s]], charge received from photodiode 302 is transferred to storage node 306 during a charge integration period; however, charge received from photodiode 302 could also be transferred to storage node 306 after the charge integration period. The storage node 306 permits a greater amount of charge to be stored than would be stored solely using the floating diffusion node 322. Consequently, the capacitive storage of the pixel is increased.